

■ PRODUCT CHARACTERISTICS

VDSS	-20V
$R_{DS(on)}$ Typ(@V _{GS} = -4.5 V)	18mΩ
$R_{DS(on)}$ typ(@V _{GS} = -2.5 V)	22mΩ
ID	-10A

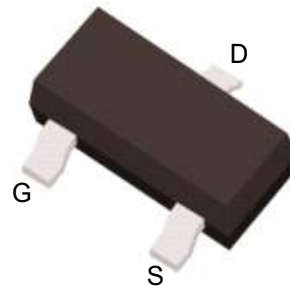
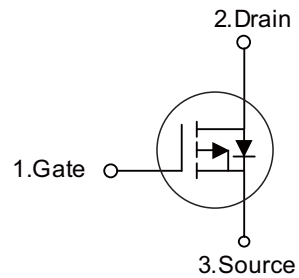
■ APPLICATIONS

- Load switch for portable
- DC/DC converter

■ FEATURES

- * High Density Cell Design For Ultra Low On-Resistance
- * Advanced trench process technology

Symbol



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT2307A3	SOT-23A-3L	3000pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±12	V
Continuous Drain Current	I _D	-10	A
Pulsed Drain Current	I _{DM}	-40	A
Maximum Power Dissipation	P _D	1.5	W
Thermal Resistance Junction-to-Ambient	R _{θJA}	83.5	°C/W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C

■ ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5	-0.7	-1.4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-3A$	-	18	25	m Ω
		$V_{GS}=-2.5V, I_D=-3A$	-	22	30	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-1A$	5	-	-	S
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V,$ $F=1.0MHz$	-	2015	-	PF
Output Capacitance	C_{oss}		-	190	-	PF
Reverse Transfer Capacitance	C_{rss}		-	173	-	PF
Switching characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=10\Omega,$ $V_{GS}=-4.5V, R_{GEN}=6\Omega$	-	4.5	-	nS
Turn-on Rise Time	t_r		-	9.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	18.7	-	nS
Turn-Off Fall Time	t_f		-	3.3	-	nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-10A, V_{GS}=-4.5V$	-	15	-	nC
Gate-Source Charge	Q_{gs}		-	1.8	-	nC
Gate-Drain Charge	Q_{gd}		-	2.8	-	nC
Drain-source diode characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-10A$	-	-	-1.2	V

■ TYPICAL CHARACTERISTICS

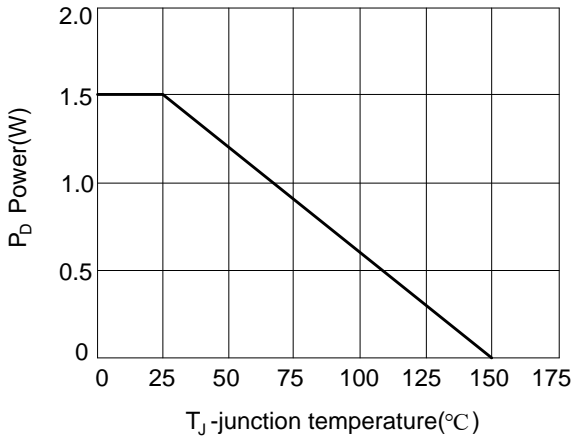


Figure 1: Power dissipation

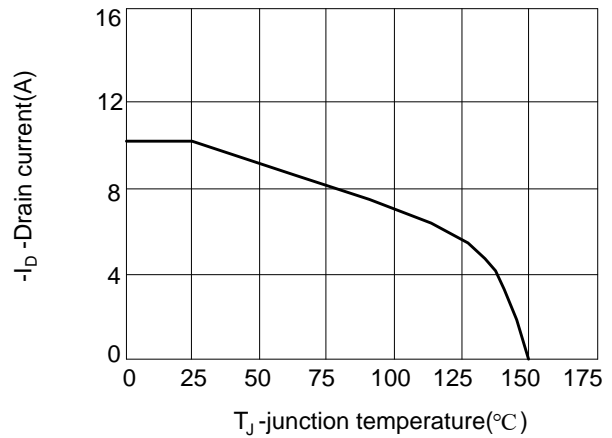


Figure 2: Drain current

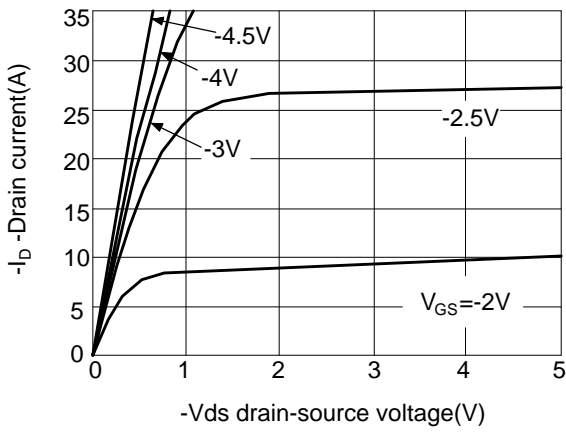


Figure 3: Output characteristics

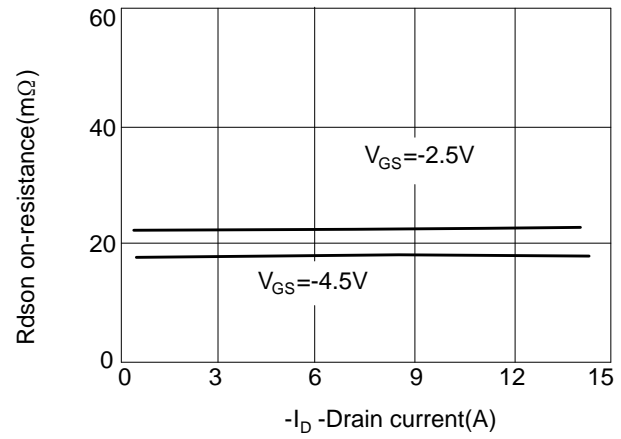


Figure 4: Drain-source on-resistance

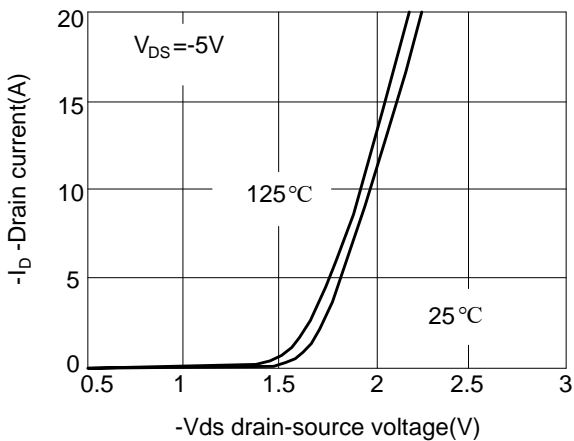


Figure 5: Transfer characteristics

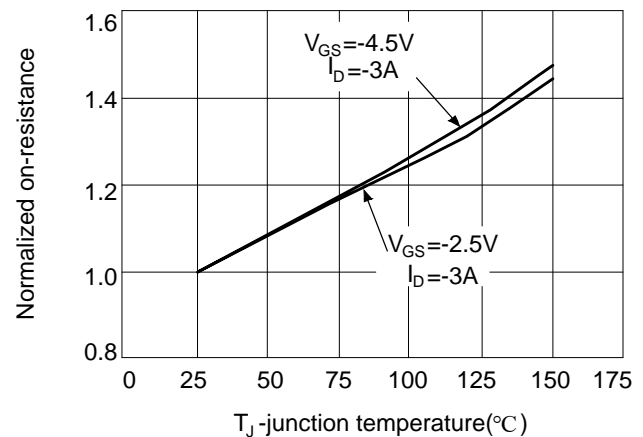


Figure 6: Drain-source on-resistance

■ TYPICAL CHARACTERISTICS(Cont.)

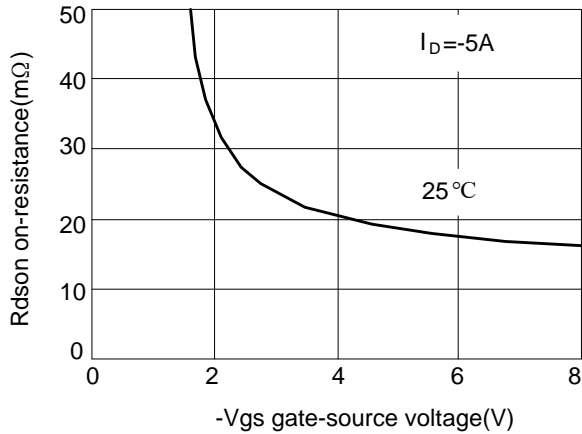


Figure 7: Rds(on) vs vgs

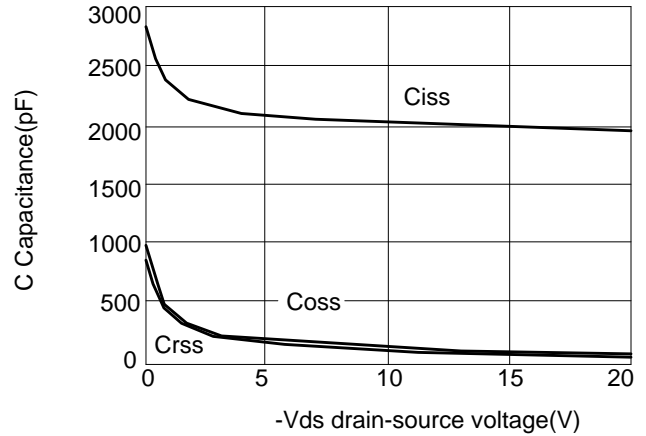


Figure 8: Capacitance vs vgs

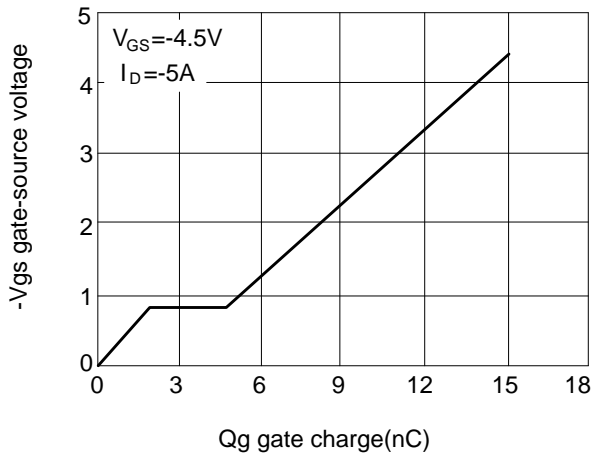


Figure 9: Gate charge

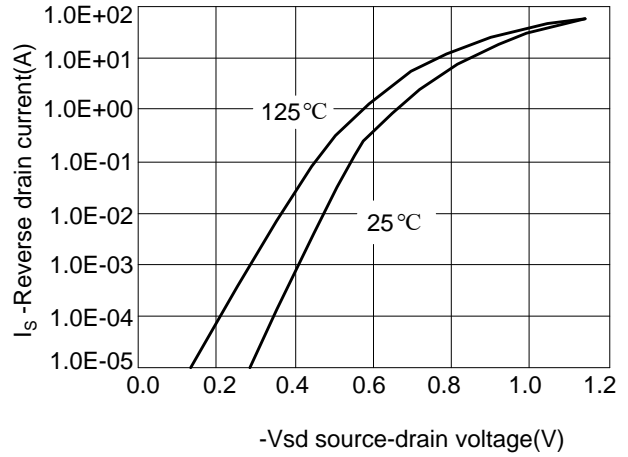


Figure 10: Source-drain diode forward

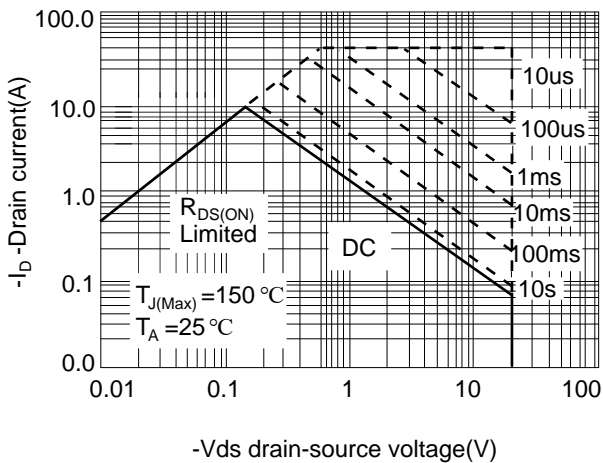


Figure 11: Safe operation area

■ TYPICAL CHARACTERISTICS(Cont.)

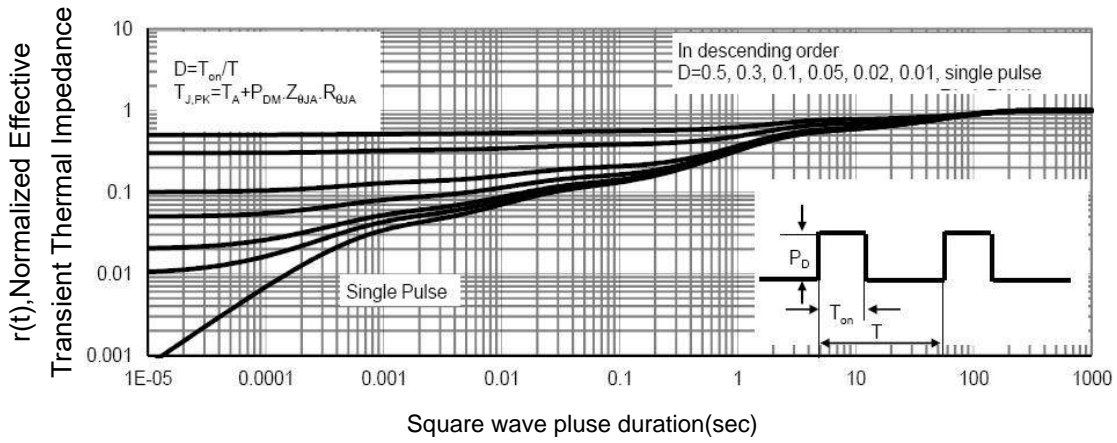


Figure 12: Normalized maximum transient thermal impedance

■ SOT-23A-3L PACKAGE OUTLINE DIMENSIONS

